N-Channel 150-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

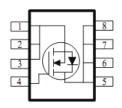
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- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
$V_{DS}(V)$ $r_{DS(on)}(m\Omega)$ $I_{D}(A)$				
150	255 @ V _{GS} = 10V	3.6		
130	290 @ V _{GS} = 4.5V	3.4		







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage			150	V		
Gate-Source Voltage	V_{GS}	±20	V			
Continuous Dusin Commenta	T _A =25°C	ı	3.6			
Continuous Drain Current ^a	T _A =70°C	l _D	2.9	Α		
Pulsed Drain Current ^b	I _{DM}	20				
Continuous Source Current (Diode Conduction) a	I _S	6.2	Α			
Device Discipation 8	T _A =25°C	P _D	5	W		
Power Dissipation ^a	T _A =70°C	I P	3.2			
Operating Junction and Storage Temperature Range			-55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	25	°C/W		
Maximum Junction-to-Ambient	Steady State	IN _θ JΑ	65			

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

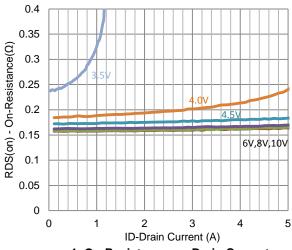
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±10	uA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			1	uA	
Zero Gate Voltage Brain Garrent	טטי				10		
On-State Drain Current	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	10			Α	
Drain-Source On-Resistance	r _{no()}	$V_{GS} = 10 \text{ V}, I_D = 2.9 \text{ A}$	255		mΩ		
Dialii-30dice Oli-Nesistance	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 2.7 \text{ A}$			290	11122	
Forward Transconductance	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 2.9 \text{ A}$		10		S	
Diode Forward Voltage	V_{SD}	$I_S = 3.1 \text{ A}, V_{GS} = 0 \text{ V}$		0.76		V	
		Dynamic					
Total Gate Charge	Q_g			10.8			
Gate-Source Charge	Q_{gs}	$V_{DS} = 75 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 2.9 \text{ A}$		3.3		nC	
Gate-Drain Charge	Q_{gd}			5.6			
Turn-On Delay Time	t _{d(on)}			10.1			
Rise Time	t _r	V_{DD} = 75 V, R_L = 25.9 Ω , I_D = 2.9 A,		10		ne	
Turn-Off Delay Time	t _{d(off)}	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		50		ns	
Fall Time	t _f			22			
Input Capacitance	C _{iss}			848			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		69		pF	
Reverse Transfer Capacitance	C_{rss}			29			

Notes

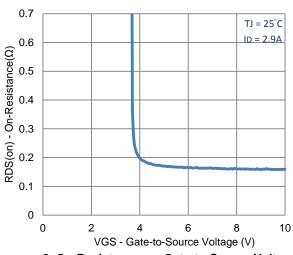
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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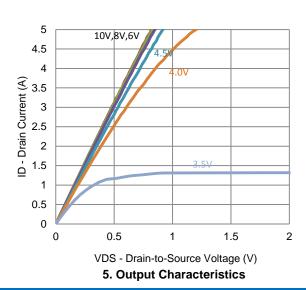
Typical Electrical Characteristics

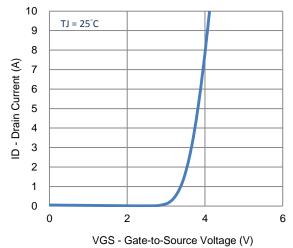


1. On-Resistance vs. Drain Current

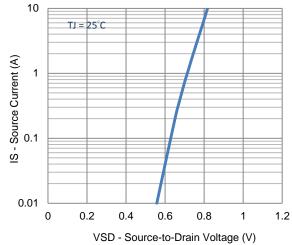


3. On-Resistance vs. Gate-to-Source Voltage

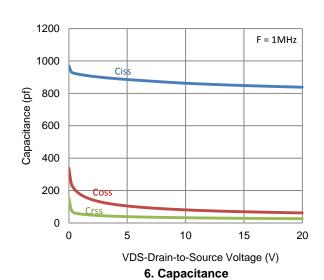




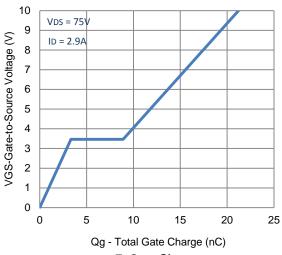
2. Transfer Characteristics

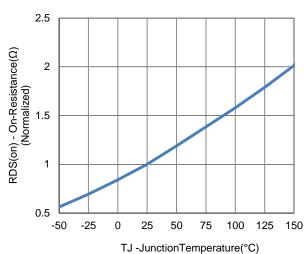


4. Drain-to-Source Forward Voltage



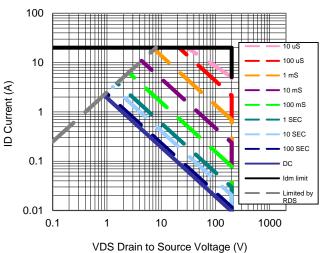
Typical Electrical Characteristics

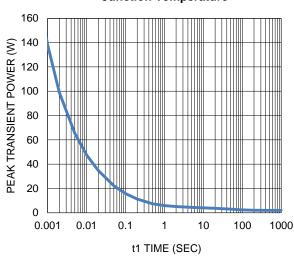




7. Gate Charge

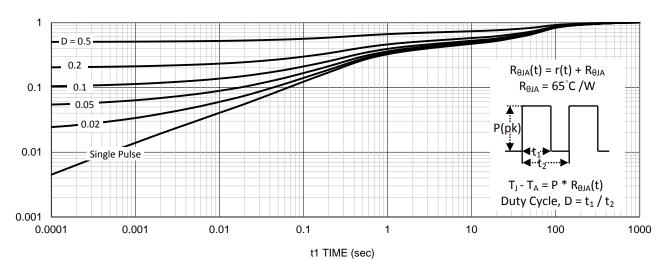






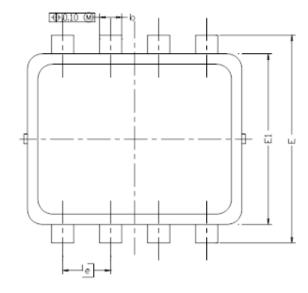
9. Safe Operating Area

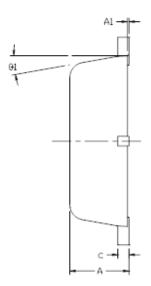
10. Single Pulse Maximum Power Dissipation

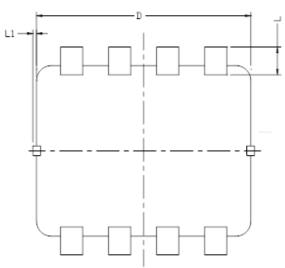


11. Normalized Thermal Transient Junction to Ambient

Package Information







DIM.	MILLIMETERS			INCHES			
DIM.	MIN	NDM	MAX	MIN	NDM	MAX	
Α	0.700	0.80	0.900	0.0276	0.0315	0.0354	
A1	0.00		0.05	0.000		0.002	
b	0,24	0,30	0,35	0.009 0.012		0.014	
	0.08	0.152	0.25	0.003	0.006	0.010	
D	2.90 BSC			0.114 BSC			
E	2.80 BSC			0.110 BSC			
E1	2.30 BSC			0.091 BSC			
9	0.65 BSC			0.026 BSC			
L	0.20	0.375	0.450	0.008	0.0148	0.0177	
L1	0		0.100	0 0		0.004	
0-1	0	10	12	0 10 1		12	